

C1 fluid comprising an ozone-containing gas and ultra pure water are sprayed onto substrates or semiconductor wafers in a treating chamber filled with ozone gas."

IN THE CLAIMS:

Please cancel claim 40 without prejudice.

Please amend claim 27 as follows:

B1
27. (Twice Amended) A method for removing organic contaminants from a substrate, comprising the steps of:

B1
contacting at least one side of said substrate with a liquid comprising water, ozone and an additive acting as a scavenger, wherein the proportion of said additive in said liquid is less than 1% molar weight of said liquid; and

C2
maintaining said liquid at a temperature less than the boiling point of said liquid.

Please add the following claims 51-60:

B1
51. A method for removing organic contaminants from a substrate, comprising the steps of:

E2
contacting at least one side of said substrate with a liquid comprising water, ozone and an additive acting as a scavenger, wherein said liquid is comprised substantially of water; and
C3
maintaining said liquid at a temperature less than the boiling point of said liquid.

52. A method as recited in claim ^{2A} 51, wherein the proportion of said additive in said liquid is less than 1% molar weight of said liquid.

24 53. A method according to claim 52, wherein the proportion of said additive in said liquid is less than 0.1% molar weight of said liquid.

25 54. A method as recited in claim 51, wherein the temperature of said liquid is between 60°C and 80°C.

26 55. A method as recited in claim 51, wherein said liquid is subjected to megasone agitation.

27 56. A method as recited in claim 51, wherein the ozone is bubbled through the liquid.

28 57. A method as recited in claim 51, wherein said additive is acting as OH radical scavenger.

29 58. A method as recited in claim 51, further comprising the step of rinsing said substrate with a solution.

30 59. A method as recited in claim 58, wherein said solution comprises de-ionised water.